Silicon NPN transistor epitaxial type
DP006

[Applications]
General purpose

[Feature]
Low collector saturation voltage VCE(sat)= 0.33V(Max.) at IC= 100mA, IB= 10mA

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	80	V
Collector-emitter voltage	VCEO	80	V
Emitter-base voltage	VEBO	4	V
Collector current	IC	0.5	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	80	-	-	V	IC= 100uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	80	-	-	V	IC= 1mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	4	-	-	V	IE= 100uA, IC= 0A
Collector-cut off current	ICEO	-	-	100	nA	VCE= 60V, IB= 0A
Collector-cut off current	ICBO	-	-	100	nA	VCB= 80V, IE= 0A
Emitter-cut off current	IEBO	-	-	100	nA	VEB= 5V, IC= 0A
DC current gain 1	hFE 1	90	-	-	-	VCE= 1V, IC= 10mA
DC current gain 2	hFE 2	90	-	-	-	VCE= 1V, IC= 100mA
Collector-emitter saturation voltage	VCE(sat)	-	-	0.33	V	IC= 100mA, IB= 10mA

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.
Notice 2) The contents described herein are subject to change without notice.